

IGBT

GD75HFT170C1S

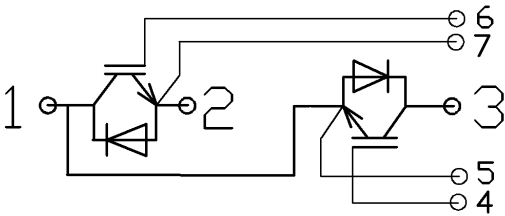
Molding Type Module

1700V/75A 2 in one-package



Features

- Low $V_{CE(sat)}$ trench IGBT technology
- Low switching losses
- 10 μ s short circuit capability
- $V_{CE(sat)}$ with positive temperature coefficient
- Low inductance case
- Fast & soft reverse recovery anti-parallel FWD
- Isolated copper baseplate using DBC technology



Equivalent Circuit Schematic

Typical Applications

- AC inverter drives mains 575-750V AC
- Public transport (auxiliary syst.)

Absolute Maximum Ratings $T_C=25^{\circ}\text{C}$ unless otherwise noted

Symbol	Description	GD75HFT170C1S	Units
V_{CES}	Collector-Emitter Voltage	1700	V

Symbol	Description	GD75HFT170C1S	Units
V_{GES}	Gate-Emitter Voltage	± 20	V
I_C	Collector Current @ $T_C=25^\circ\text{C}$ @ $T_C=80^\circ\text{C}$	140	A
		75	
$I_{CM(1)}$	Pulsed Collector Current $t_p=1\text{ms}$	150	A
I_F	Diode Continuous Forward Current	75	A
I_{FM}	Diode Maximum Forward Current	150	A
P_D	Maximum Power Dissipation @ $T_J=175^\circ\text{C}$	600	W
T_{SC}	Short Circuit Withstand Time @ $T_J=125^\circ\text{C}$	10	μs
T_{jmax}	Maximum Junction Temperature	175	$^\circ\text{C}$
T_{STG}	Storage Temperature Range	-40 to +125	$^\circ\text{C}$
$I^2t\text{-value, Diode}$	$V_R=0\text{V}, t=10\text{ms}, T_J=125^\circ\text{C}$	1050	A^2s
V_{ISO}	Isolation Voltage RMS, $f=50\text{Hz}, t=1\text{min}$	4000	V
Mounting Torque	Power Terminal Screw:M5	2.5 to 5.0	N.m
	Mounting Screw:M6	3.0 to 5.0	N.m

Notes:

(1) Repetitive rating: Pulse width limited by max. junction temperature

Electrical Characteristics of IGBT $T_C=25^\circ\text{C}$ unless otherwise noted**Off Characteristics**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV_{CES}	Collector-Emitter Breakdown Voltage	$V_{GE}=0\text{V}, I_C=3.0\text{mA}, T_J=25^\circ\text{C}$	1700			V
I_{CES}	Collector Cut-Off Current	$V_{CE}=V_{CES}, V_{GE}=0\text{V}, T_J=25^\circ\text{C}$			3.0	mA
I_{GES}	Gate-Emitter Leakage Current	$V_{GE}=V_{GES}, V_{CE}=0\text{V}, T_J=25^\circ\text{C}$			400	nA

On Characteristics

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
$V_{GE(th)}$	Gate-Emitter Threshold Voltage	$I_C=3.0\text{mA}, V_{CE}=V_{GE}, T_J=25^\circ\text{C}$	5.2	5.8	6.4	V
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	$I_C=75\text{A}, V_{GE}=15\text{V}, T_J=25^\circ\text{C}$		2.0		V
		$I_C=75\text{A}, V_{GE}=15\text{V}, T_J=125^\circ\text{C}$		2.4		

Switching Characteristics

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
$t_{d(on)}$	Turn-On Delay Time	$V_{CC}=900\text{V}, I_C=75\text{A}, R_G=6.8\Omega, V_{GE}=\pm 15\text{V}, T_J=25^\circ\text{C}$		370		ns
t_r	Rise Time			40		ns
$t_{d(off)}$	Turn-Off Delay Time			650		ns

GD75HFT170C1S**IGBT Module**

t_f	Fall Time	$V_{CC}=900V, I_C=75A,$ $R_G=6.8\Omega, V_{GE}=\pm 15V,$ $T_J=25^\circ C$		180		ns
E_{on}	Turn-On Switching Loss			16.5		mJ
E_{off}	Turn-Off Switching Loss			16.0		mJ
$t_{d(on)}$	Turn-On Delay Time	$V_{CC}=900V, I_C=75A,$ $R_G=6.8\Omega, V_{GE}=\pm 15V,$ $T_J=125^\circ C$		400		ns
t_r	Rise Time			50		ns
$t_{d(off)}$	Turn-Off Delay Time			800		ns
t_f	Fall Time			300		ns
E_{on}	Turn-On Switching Loss			24.0		mJ
E_{off}	Turn-Off Switching Loss			23.5		mJ
C_{ies}	Input Capacitance	$V_{CE}=25V, f=1MHz,$ $V_{GE}=0V$		6.80		nF
C_{oes}	Output Capacitance			0.28		nF
C_{res}	Reverse Transfer Capacitance			0.22		nF
I_{SC}	SC Data	$t_{SC}\leq 10\mu s, V_{GE}=15V,$ $T_J=125^\circ C, V_{CC}=1000V,$ $V_{CEM}\leq 1700V$		300		A
R_{Gint}	Internal Gate Resistance			8.5		Ω
L_{CE}	Stray Inductance				30	nH
$R_{CC'+EE'}$	Module Lead Resistance, Terminal to Chip	$T_C=25^\circ C$		0.75		m Ω

Electrical Characteristics of DIODE $T_C=25^\circ C$ unless otherwise noted

Symbol	Parameter	Test Conditions		Min.	Typ.	Max.	Units
V _F	Diode Forward Voltage	I _F =75A	T _J =25°C		1.80		V
			T _J =125°C		1.90		
Q _r	Diode Reverse Recovery Charge	I _F =75A, V _R =900V, di/dt=-1800A/μs, V _{GE} =-15V	T _J =25°C		22.0		μC
			T _J =125°C		36.5		
I _{RM}	Diode Peak Reverse Recovery Current		T _J =25°C		115		A
			T _J =125°C		125		
E _{rec}	Reverse Recovery Energy		T _J =25°C		11.5		mJ
			T _J =125°C		20.5		

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case (IGBT Part, per 1/2 Module)		0.25	K/W
$R_{\theta JC}$	Junction-to-Case (DIODE Part, per 1/2 Module)		0.46	K/W
$R_{\theta CS}$	Case-to-Sink (Conductive grease applied)	0.05		K/W
Weight	Weight of Module	150		g

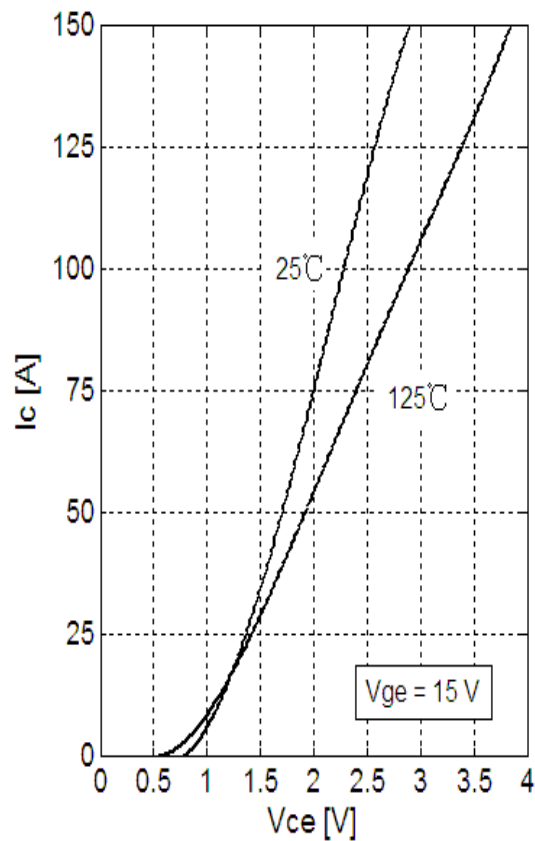


Fig 1. IGBT Typical Output Characteristics

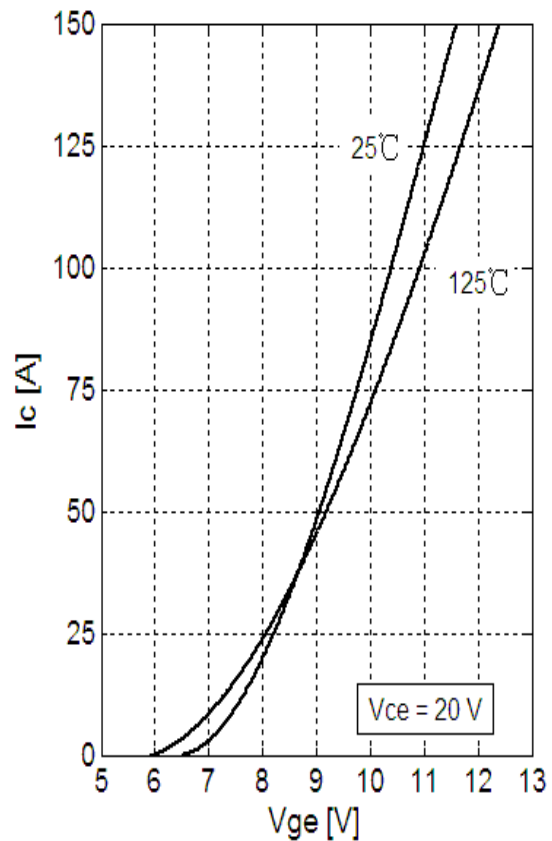


Fig 2. IGBT Typical Transfer Characteristics

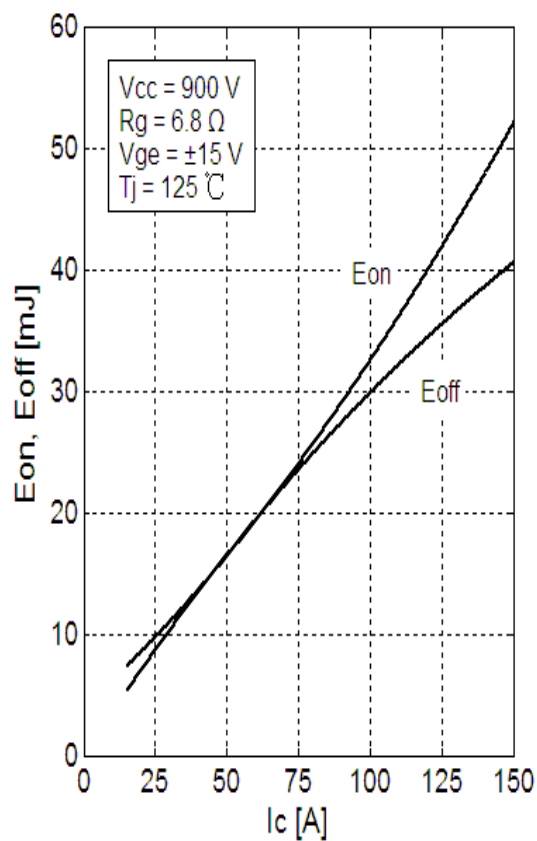


Fig 3. IGBT Switching Loss vs. Collector Current

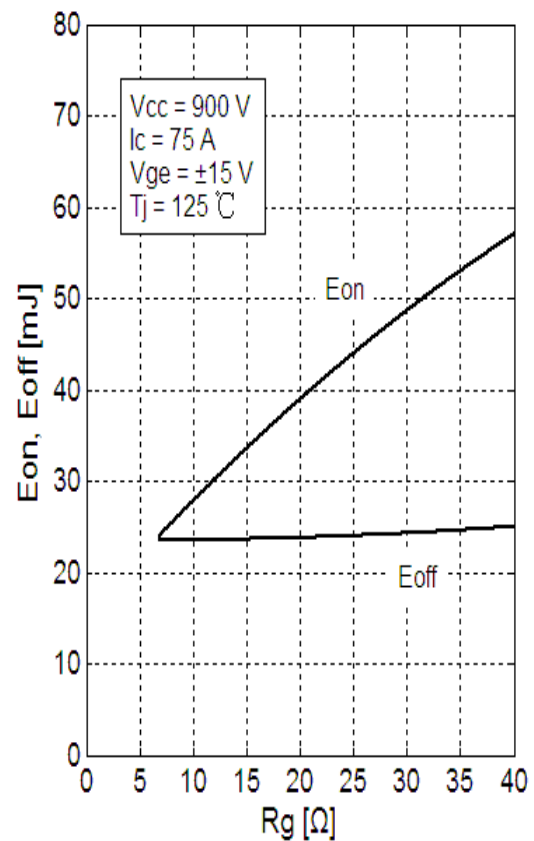


Fig 4. IGBT Switching Loss vs. Gate Resistor

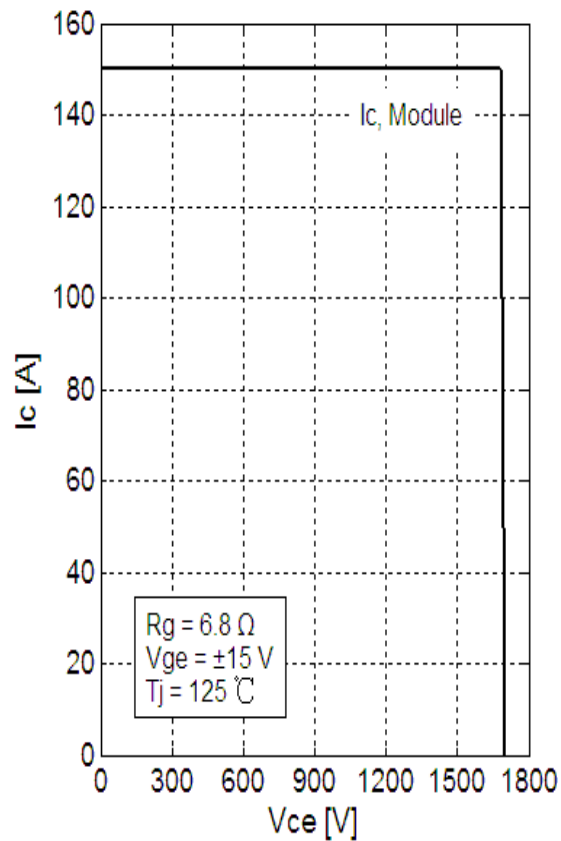


Fig 5. RBSOA

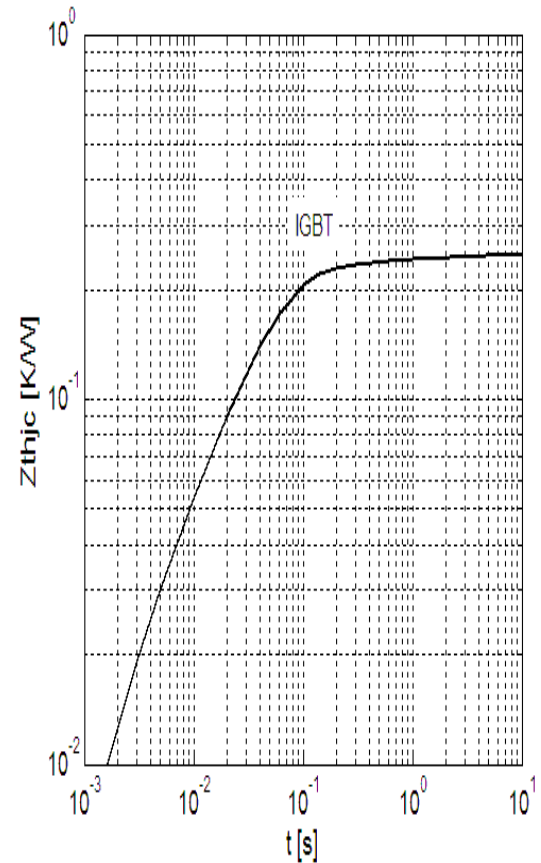


Fig 6. IGBT Transient Thermal Impedance

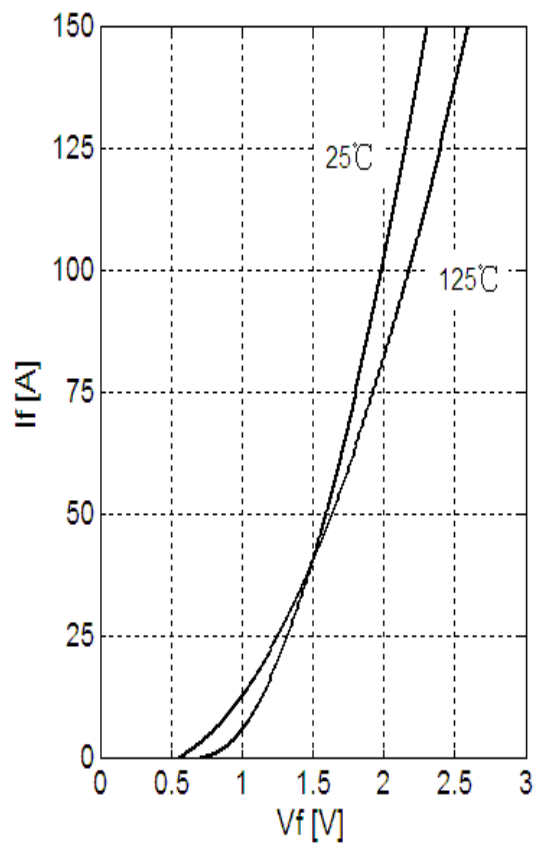


Fig 7. Forward Characteristics of Diode

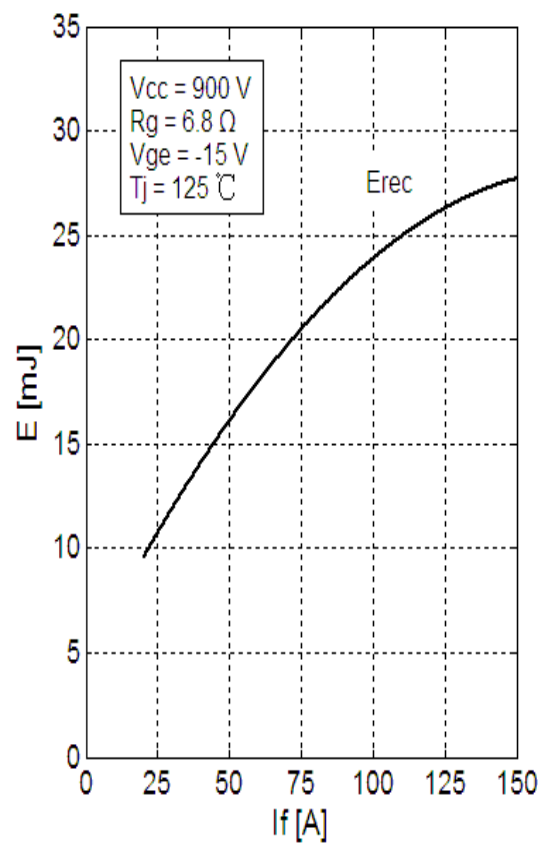


Fig 8. Diode Switching Loss vs. Collector Current

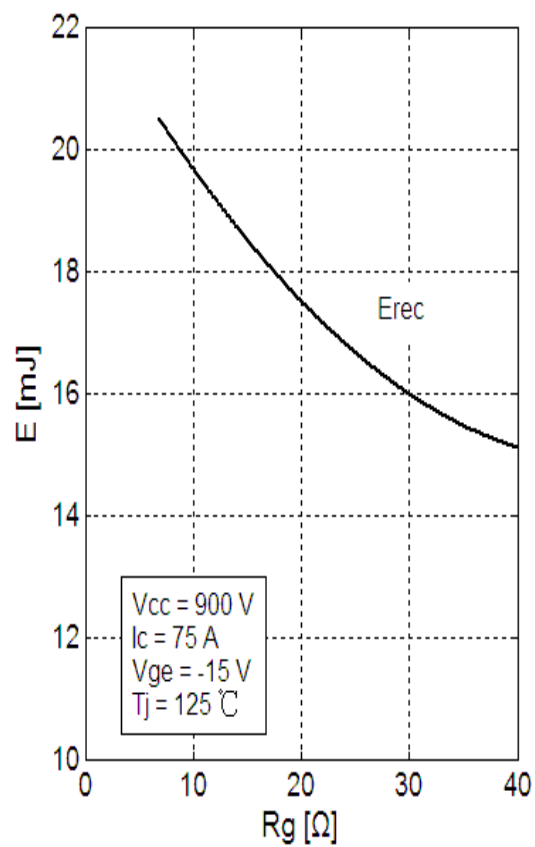


Fig9. Diode Switching Loss vs. Gate Resistor

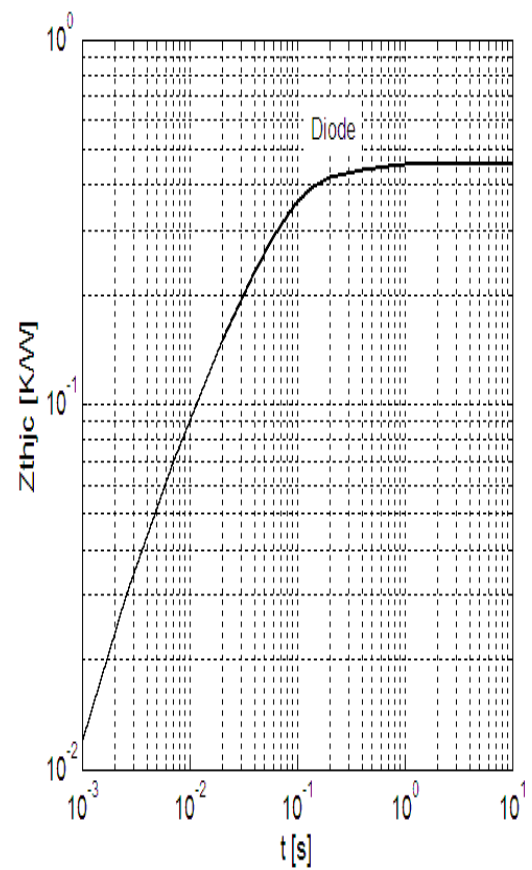


Fig 10. Diode Transient Thermal Impedance

Package Dimension

Dimensions in Millimeters

